

20V N-Channel Enhancement Mode MOSFET - ESD Protected

Voltage 20 V Current 1A

Features

- RDS(ON), VGS@4.5V, ID@1.0A<150mΩ
- RDS(ON), VGS@2.5V, ID@0.7A<215mΩ
- RDS(ON), VGS@1.8V, ID@0.3A<400mΩ
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std.(Halogen Free)

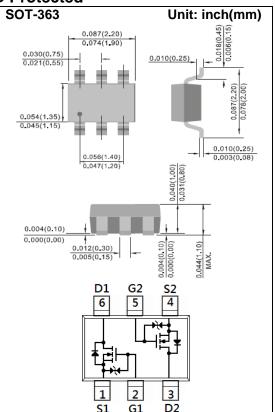
Mechanical Data

• Case: SOT-363 Package

Terminals: Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0002 ounces, 0.006 grams

Marking: T00



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	20	V
Gate-Source Voltage		V _{GS}	<u>+</u> 8	V
Continuous Drain Current		ID	1	А
Pulsed Drain Current (Note 4)		I _{DM}	4	А
Power Dissipation	T _a =25°C	_	350	mW
	Derate above 25°C	P _D	2.8	mW/°C
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C
Typical Thermal resistance - Junction to Ambient (Note 3)		Reja	357	°C/W



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	20	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} , I _D =250uA	0.5	0.8	1.0	V	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =1A	-	120	150	mΩ	
		V _{GS} =2.5V, I _D =0.7A	-	160	215		
		V _{GS} =1.8V, I _D =0.3A	-	260	400		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V	-	0.01	1	uA	
Gate-Source Leakage Current	Igss	V _{GS} = <u>+</u> 8V, V _{DS} =0V	-	<u>+</u> 2	<u>+</u> 10	uA	
Dynamic ^(Note 5)							
Total Gate Charge	Q_g	\/ 40\/ L 4A	-	1.6	-	nC	
Gate-Source Charge	Q_{gs}	V _{DS} =10V, I _D =1A,	-	0.31	-		
Gate-Drain Charge	Q_gd	V _{GS} =4.5V (Note 1,2)	-	0.41	-		
Input Capacitance	Ciss	\/ 40\/ \/ 0\/	-	92	-	pF	
Output Capacitance	Coss	V _{DS} =10V, V _{GS} =0V,	-	25	-		
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	9.1	-		
Turn-On Delay Time	td _(on)	101/ 10	-	5.8	-		
Turn-On Rise Time	tr	V _{DD} =10V, I _D =1A,	-	25.8	-		
Turn-Off Delay Time	td _(off)	$V_{GS}=4.5V$, $R_{G}=6\Omega$ (Note 1,2)	-	42	-	ns	
Turn-Off Fall Time	tf	RG=012 (Note 1,2)	-	32	-		
Drain-Source Diode							
Maximum Continuous Drain-Source Diode Forward Current	Is		-	-	1	А	
Diode Forward Voltage	V _{SD}	Is=1.0A, V _{GS} =0V	-	0.85	1.2	V	

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
- 4. The maximum current rating is package limited
- 5. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

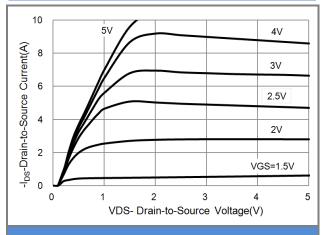


Fig.1 On-Region Characteristics

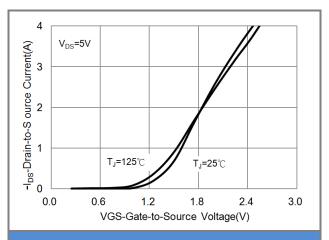


Fig.2 Transfer Characteristics

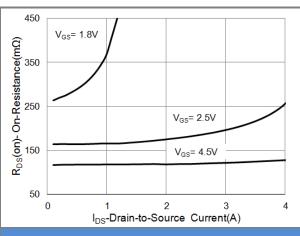


Fig.3 On-Resistance vs. Drain Current

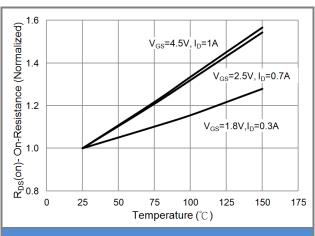
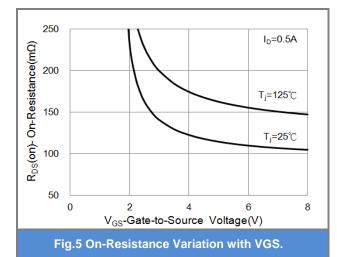
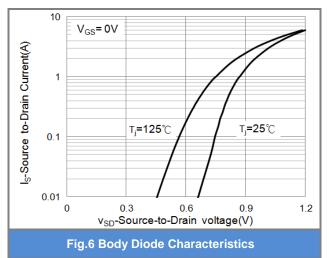


Fig.4 On-Resistance vs. Junction temperature







TYPICAL CHARACTERISTIC CURVES

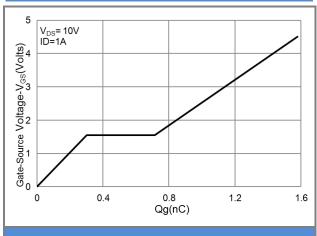


Fig.7 Gate-Charge Characteristics

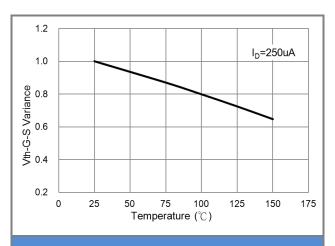


Fig.8 Threshold Voltage Variation with Temperature.

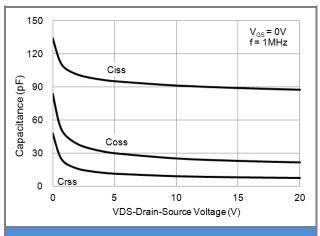


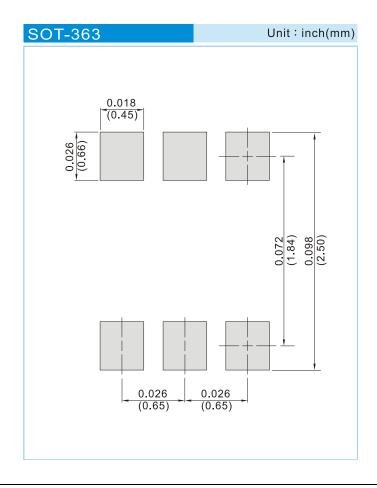
Fig.9 Capacitance vs. Drain-Source Voltage.



Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJT7800	SOT-363	3K pcs / 7" reel	Т00
PJT7800	SOT-363	10K pcs / 13" reel	Т00

Mounting Pad Layout





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